Rajesh Sathiyanarayanan

List of Publications by Year
in descending order

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11	124	1478505 6	1372567 10
papers	citations	h-index	g-index

11	11	11	208
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Role of Solvent in the Shape-Controlled Synthesis of Anisotropic Colloidal Nanostructures. Journal of Physical Chemistry C, 2011, 115, 18983-18990.	3.1	36
2	Role of point defects and HfO2/TiN interface stoichiometry on effective work function modulation in ultra-scaled complementary metalâ€“oxideâ€“semiconductor devices. Journal of Applied Physics, 2013, 114, .	2.5	21
3	Role of codeposited impurities during growth. I. Explaining distinctive experimental morphology on Cu(0 0 1). Physical Review B, 2011, 83, .	3.2	14
4	Role of codeposited impurities during growth. II. Dependence of morphology on binding and barrier energies. Physical Review B, 2011, 83, .	3.2	14
5	Ab-initio calculations of interactions between Cu adatoms on Cu(110): Sensitivity of strong multi-site interactions to adatom relaxations. Surface Science, 2009, 603, 2387-2392.	1.9	12
6	Sensitivity of short-range trio interactions to lateral relaxation of adatoms: Challenges for detailed lattice-gas modeling. Surface Science, 2008, 602, 1243-1249.	1.9	11
7	Dielectric properties of Si3â^'Î¾GeÎ¾N4 and Si3â^'Î¾CÎ¾N4: A density functional study. Journal of Applied Physics, 2013, 113, 234102.	2.5	6
8	Terrace-width distributions of touching steps: Modification of the fermion analogy with implications for measuring step-step interactions. Physical Review B, 2009, 80, .	3.2	5
9	Nitrogen diffusion in hafnia and the impact of nitridation on oxygen and hydrogen diffusion: A first-principles study. Journal of Applied Physics, 2015, 117, 034303.	2.5	4
10	Stoichiometry tuning of TaN films through ion treatment: Molecular dynamics study. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	1
11	Impact of oxygen plasma on nitrided and annealed atomic layer deposited SiO2/high-k/metal gate for high-voltage input and output fin-shaped field effect transistor devices. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, 012202.	1.2	0